

**UHF power transistor**

**BLU30**

**DESCRIPTION**

N-P-N silicon planar epitaxial transistor primarily intended for use in mobile radio transmitters in the 470 MHz communications band.

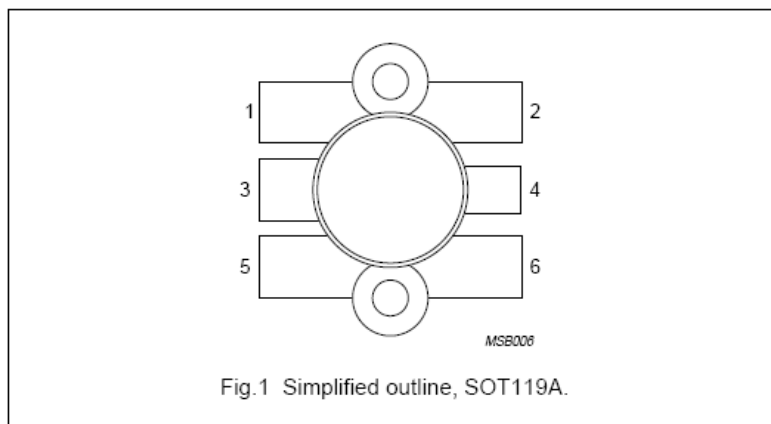
**FEATURES:**

- \* Multi-base structure and emitter-ballasting resistors for an optimum temperature profile
- \* Gold metallization ensures excellent reliability
- \* Internal matching to achieve an optimum wideband capability and high power gain
- \* The transistor has a 6-lead flange envelope with a ceramic cap (SOT-119).

**Specifications:**

|                                  |                 |
|----------------------------------|-----------------|
| Envelope                         | SOT-119         |
| Mode of operation                | class-B; c.w.   |
| Collector-emitter voltage (d.c.) | $V_{CE}$ 12,5 V |
| Frequency                        | f 470 MHz       |
| Load power                       | $P_L$ 30 W      |
| Power gain                       | $G_P$ > 6,0 dB  |
| Collector efficiency             | $\eta_C$ > 55 % |
| Heatsink temperature             | $T_h$ 25 °C     |

**Drawings:**



| PIN | DESCRIPTION |
|-----|-------------|
| 1   | emitter     |
| 2   | emitter     |
| 3   | base        |
| 4   | collector   |
| 5   | emitter     |
| 6   | emitter     |